(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
11 December 2003 (11.12.2003)

PCT

(10) International Publication Number
WO 2003/103032 A3

(51) International Patent Classification[7]: H01L 21/28, 21/336, 21/8234, 21/8238

(21) International Application Number: PCT/US2003/016307

(22) International Filing Date: 22 May 2003 (22.05.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/159,520 31 May 2002 (31.05.2002) US

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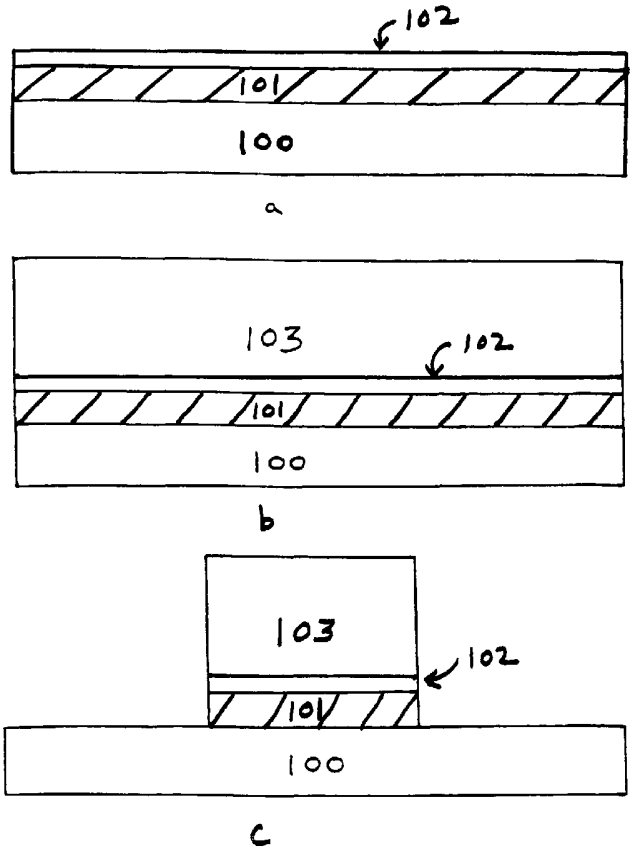
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(81) Designated States *(national)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States *(regional)*: ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

[Continued on next page]

(54) Title: A METHOD FOR MAKING A SEMICONDUCTOR DEVICE HAVING A HIGH-K GATE DIELECTRIC



(57) Abstract: A method for making a semiconductor device is described. That method comprises forming on a substrate (100) a dielectric layer (101) that has a dielectric constant that is greater than the dielectric constant of silicon dioxide. An insulating layer (102), which is compatible with the dielectric layer and a gate electrode to be formed on the insulating layer, is formed on the dielectric layer, and a gate electrode (103) is then formed on the insulating layer.

WO 2003/103032 A3

Published:
— *with international search report*
— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

(88) Date of publication of the international search report:
5 February 2004

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

INTERNATIONAL SEARCH REPORT

Internatio plication No
PCT/US 03/16307

A. CLASSIFICATION OF SUBJECT MATTER
IPC 7 H01L21/28 H01L21/336 H01L21/8234 H01L21/8238

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)
IPC 7 H01L

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)
EPO-Internal, PAJ, WPI Data

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category °	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
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Y		3-5, 11-20
X	US 2002/048885 A1 (SHIBATA YOSHIYUKI) 25 April 2002 (2002-04-25) paragraphs '0072!-'0074!	1,2
Y	US 6 200 866 B1 (EVANS DAVID R ET AL) 13 March 2001 (2001-03-13) column 1, line 62-64 column 6, line 21-29,31,32	3-5, 11-20

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Date of the actual completion of the international search	Date of mailing of the international search report
14 November 2003	03/12/2003

Name and mailing address of the ISA	Authorized officer
European Patent Office, P.B. 5818 Patentlaan 2 NL – 2280 HV Rijswijk Tel. (+31–70) 340–2040, Tx. 31 651 epo nl, Fax: (+31–70) 340–3016	Kenevey, K

INTERNATIONAL SEARCH REPORT

Information on patent family members

Internatio plication No
PCT/US 03/16307

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